

Abstract:**Method and Device for Producing Semiconductor Wafers of Silicon**

5 Method for producing semiconductor wafers of silicon,
comprising the pulling of a single crystal from a melt
contained in a crucible and the slicing of semiconductor wafers
from the pulled single crystal, heat being delivered to a
center of the growing single crystal at the boundary with the
10 melt during the pulling of the single crystal, and a CUSP
magnetic field being applied to the melt so that a neutral
surface of the CUSP magnetic field intersects a pulling axis of
the single crystal at a distance of at least 50 mm from a
surface of the melt. The invention also relates to a device for
15 carrying out the method.